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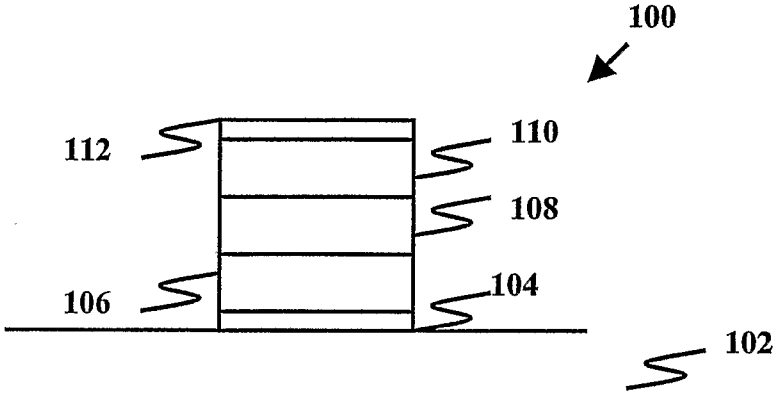
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(54) Title: MEMORY GATE STACK STRUCTURE




(57) Abstract: A memory gate stack structure (100) comprising a substrate layer (102) comprising a silicon-based material, a tunnel layer (104) formed on the substrate layer, a charge storage layer (106) formed on the tunnel layer and comprising a hafnium-aluminium-oxide-based material, a blocking layer (108) formed on the charge storage layer, and a gate layer (110) formed on the blocking layer.